GUJARAT TECHNOLOGICAL UNIVERSITY ME – SEMESTER IV (NEW) – • EXAMINATION – SUMMER 2016

C	 .	ME = SEMESTER TV (TEW) = * EXAMINATION = SUMMER 2010	17	
Subject Code: 2/44202 Date:04/			10	
Su	bject	Name: Power Efficient VLSI Design	-	
Time:10:30 am to 01:00 pm Total M		J:30 am to 01:00 pm Total Marks:	arks: 70	
Ins	tructio 1. 2. 3.	ns: Attempt all questions. Make suitable assumptions wherever necessary. Figures to the right indicate full marks.		
Q.1	(a) (b)	Explain in detail source of power dissipation in CMOS. Why n-well CMOS Process? Why not p-well CMOS Process?	07 07	
Q.2	(a) (b)	Explain Self-Reverse Biasing. Explain low dynamic power techniques.	07 07	
	(b)	UK Discuss Telerable Skow w/s Zero Skow	07	
	(U)	Discuss Tolerable Skew V/S Zero Skew.	07	
Q.3	(a)	Derive mathematical expression to avoid negative tolerable skew and positive tolerable skew.	07	
	(b)	Illustrate the effect of wire widening and intermediate buffer insertion on delay reduction using mathematical expression.	07	
	<i>(</i>)	OR	•-	
Q.3	(a) (b)	Discuss data retention power sources for DRAM and SRAM. Discuss Monte Carlo Simulation Technique for power estimation with necessary expressions.	07 07	
Q.4	(a)	What is Glitch? Discuss various techniques used for glitch reduction in low power design.	07	
	(b)	Explain Power and Performance Management. OR	07	
Q.4	(a)	Discuss in brief the effect of transistor and gate sizing for Power Efficient VLSI Design.	07	
	(b)	Explain algorithm level analysis and optimization.	07	
Q.5	(a) (b)	Discuss architectural level estimation and synthesis. Compare SPICE simulation based power simulation v/s statistical based power estimation techniques.	07 07	
		OR		
Q.5	(a)	Discuss the effect of process variation on the performance of clock distribution network.	07	
	(b)	Explain Multi -V _T Technique.	07	
